

# Hans Reisinger

## List of Publications by Year in descending order

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27  
papers

1,263  
citations

933447

10  
h-index

1199594

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g-index

27  
all docs

27  
docs citations

27  
times ranked

563  
citing authors

#	ARTICLE	IF	CITATIONS
1	Optical Emission Correlated to Bias Temperature Instability in SiC MOSFETs. , 2022, , .		6
2	Efficient Evaluation of the Time-Dependent Threshold Voltage Distribution Due to NBTI Stress Using Transistor Arrays. , 2022, , .		2
3	On the Physical Meaning of Single-Value Activation Energies for BTI in Si and SiC MOSFET Devices. IEEE Transactions on Electron Devices, 2021, 68, 236-243.	3.0	10
4	Physical Modeling of Charge Trapping in 4H-SiC DMOSFET Technologies. IEEE Transactions on Electron Devices, 2021, 68, 4016-4021.	3.0	22
5	The Impact of Interfacial Charge Trapping on the Reproducibility of Measurements of Silicon Carbide MOSFET Device Parameters. Crystals, 2020, 10, 1143.	2.2	6
6	Mixed Hot-Carrier/Bias Temperature Instability Degradation Regimes in Full $\{V_G, V_D\}$ Bias Space: Implications and Peculiarities. IEEE Transactions on Electron Devices, 2020, 67, 3315-3322.	3.0	20
7	An Efficient Analog Compact NBTI Model for Stress and Recovery Based on Activation Energy Maps. IEEE Transactions on Electron Devices, 2019, 66, 4623-4630.	3.0	10
8	Review on SiC MOSFETs High-Voltage Device Reliability Focusing on Threshold Voltage Instability. IEEE Transactions on Electron Devices, 2019, 66, 4604-4616.	3.0	101
9	NBTI Degradation and Recovery in Analog Circuits: Accurate and Efficient Circuit-Level Modeling. IEEE Transactions on Electron Devices, 2019, 66, 1662-1668.	3.0	18
10	Impact of Mixed Negative Bias Temperature Instability and Hot Carrier Stress on MOSFET Characteristics – Part I: Experimental. IEEE Transactions on Electron Devices, 2019, 66, 232-240.	3.0	22
11	Understanding BTI in SiC MOSFETs and Its Impact on Circuit Operation. IEEE Transactions on Device and Materials Reliability, 2018, 18, 144-153.	2.0	70
12	Fast acquisition of activation energy maps using temperature ramps for lifetime modeling of BTI. , 2018, , .		4
13	Voltage-Dependent Activation Energy Maps for Analytic Lifetime Modeling of NBTI Without Time Extrapolation. IEEE Transactions on Electron Devices, 2018, 65, 4764-4771.	3.0	12
14	Understanding and modeling transient threshold voltage instabilities in SiC MOSFETs. , 2018, , .		36
15	On the influence of BTI and HCI on parameter variability. , 2017, , .		12
16	Circuit relevant HCS lifetime assessments at single transistors with emulated variable loads. , 2017, , .		11
17	Threshold voltage hysteresis in SiC MOSFETs and its impact on circuit operation. , 2017, , .		23
18	Analog-circuit NBTI degradation and time-dependent NBTI variability: An efficient physics-based compact model. , 2016, , .		6

#	ARTICLE	IF	CITATIONS
19	NBTI in Nanoscale MOSFETsâ€”The Ultimate Modeling Benchmark. IEEE Transactions on Electron Devices, 2014, 61, 3586-3593.	3.0	49
20	Physical modeling of NBTI: From individual defects to devices. , 2014, , .		15
21	Analytic modeling of the bias temperature instability using capture/emission time maps. , 2011, , .		136
22	Understanding and modeling AC BTI. , 2011, , .		76
23	The statistical analysis of individual defects constituting NBTI and its implications for modeling DC- and AC-stress. , 2010, , .		167
24	The time dependent defect spectroscopy (TDDS) for the characterization of the bias temperature instability. , 2010, , .		226
25	A Study of NBTI and Short-Term Threshold Hysteresis of Thin Nitrided and Thick Non-Nitrided Oxides. IEEE Transactions on Device and Materials Reliability, 2009, 9, 106-114.	2.0	15
26	Analysis of NBTI Degradation- and Recovery-Behavior Based on Ultra Fast VT-Measurements. , 2006, , .		188
27	Performance Analysis of 4H-SiC Pseudo-D CMOS Inverter Circuits Employing Physical Charge Trapping Models. Materials Science Forum, 0, 1062, 688-695.	0.3	0